

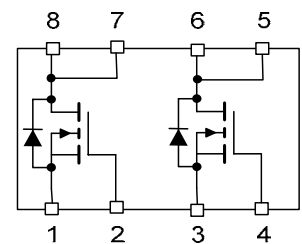
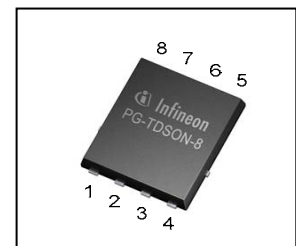
OptiMOS® Power-Transistor

Features

- Dual N-channel Logic Level - Enhancement mode
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested

Product Summary

| | | |
|-----------------------|----|----|
| V_{DS} | 55 | V |
| $R_{DS(on),max}^{4)}$ | 50 | mΩ |
| I_D | 20 | A |

PG-TDSON-8-4


| Type | Package | Marking |
|----------------|--------------|---------|
| IPG20N06S2L-50 | PG-TDSON-8-4 | 2N06L50 |

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|--|----------------|--|--------------|------|
| Continuous drain current one channel active ²⁾ | I_D | $T_C=25\text{ °C}$, $V_{GS}=10\text{ V}^{1)}$ | 20 | A |
| | | $T_C=100\text{ °C}$, $V_{GS}=10\text{ V}$ | 16 | |
| Pulsed drain current ²⁾ one channel active | $I_{D,pulse}$ | - | 80 | |
| Avalanche energy, single pulse ^{2, 4)} | E_{AS} | $I_D=10\text{ A}$ | 60 | mJ |
| Avalanche current, single pulse ⁴⁾ | I_{AS} | - | 15 | A |
| Gate source voltage | V_{GS} | - | ±20 | V |
| Power dissipation one channel active | P_{tot} | $T_C=25\text{ °C}$ | 51 | W |
| Operating and storage temperature | T_j, T_{stg} | - | -55 ... +175 | °C |
| IEC climatic category; DIN IEC 68-1 | - | - | 55/175/56 | |

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|------------|--|--------|------|------|------|
| | | | min. | typ. | max. | |
| Thermal characteristics²⁾ | | | | | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | - | 2.9 | K/W |
| SMD version, device on PCB | R_{thJA} | minimal footprint | - | 100 | - | |
| | | 6 cm ² cooling area ³⁾ | - | 60 | - | |

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

| | | | | | | |
|--|---------------|---|-----|------|-----|------------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$ | 55 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=19\text{ }\mu\text{A}$ | 1.2 | 1.6 | 2.0 | |
| Zero gate voltage drain current ⁴⁾ | I_{DSS} | $V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$ | - | 0.01 | 1 | μA |
| | | $V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}^{2)}$ | - | 1 | 100 | |
| Gate-source leakage current ⁴⁾ | I_{GSS} | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$ | - | 1 | 100 | nA |
| Drain-source on-state resistance ⁴⁾ | $R_{DS(on)}$ | $V_{GS}=4.5\text{ V}, I_D=10\text{ A}$ | - | 50 | 60 | $\text{m}\Omega$ |
| | | $V_{GS}=10\text{ V}, I_D=15\text{ A}$ | - | 39 | 50 | |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics²⁾

| | | | | | | |
|--|--------------|---|---|-----|-----|----|
| Input capacitance ⁴⁾ | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$ | - | 430 | 560 | pF |
| Output capacitance ⁴⁾ | C_{oss} | | - | 120 | 160 | |
| Reverse transfer capacitance ⁴⁾ | C_{rss} | | - | 45 | 68 | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=27.5\text{ V},$ $V_{GS}=10\text{ V}, I_D=20\text{ A},$ $R_G=11\ \Omega$ | - | 2 | - | ns |
| Rise time | t_r | | - | 3 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 15 | - | |
| Fall time | t_f | | - | 10 | - | |

Gate Charge Characteristics^{2, 4)}

| | | | | | | |
|-----------------------|---------------|--|---|-----|-----|----|
| Gate to source charge | Q_{gs} | $V_{DD}=44\text{ V}, I_D=20\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 1.5 | 2 | nC |
| Gate to drain charge | Q_{gd} | | - | 4.6 | 6.9 | |
| Gate charge total | Q_g | | - | 13 | 17 | |
| Gate plateau voltage | $V_{plateau}$ | | - | 3.7 | - | V |

Reverse Diode

| | | | | | | |
|--|---------------|---|---|-----|-----|----|
| Diode continuous forward current ²⁾ one channel active | I_S | $T_C=25\text{ }^\circ\text{C}$ | - | - | 20 | A |
| Diode pulse current ²⁾ one channel active | $I_{S,pulse}$ | | - | - | 80 | |
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=15\text{ A},$ $T_j=25\text{ }^\circ\text{C}$ | - | 1.0 | 1.3 | V |
| Reverse recovery time ²⁾ | t_{rr} | $V_R=27.5\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 25 | - | ns |
| Reverse recovery charge ^{2, 4)} | Q_{rr} | | - | 24 | - | nC |

¹⁾ Current is limited by bondwire; with an $R_{thJC}=2.9\text{ K/W}$ the chip is able to carry 23A at 25°C.

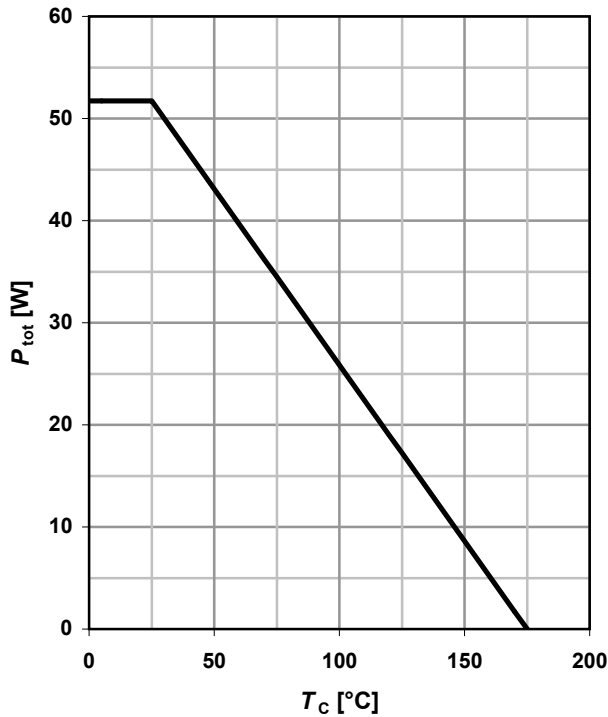
²⁾ Specified by design. Not subject to production test.

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

⁴⁾ Per channel

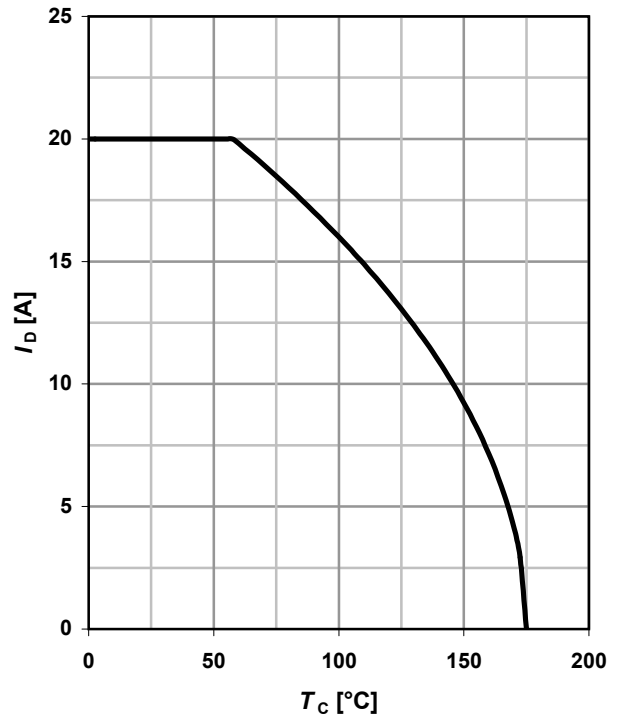
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \geq 6\text{ V}$; one channel active



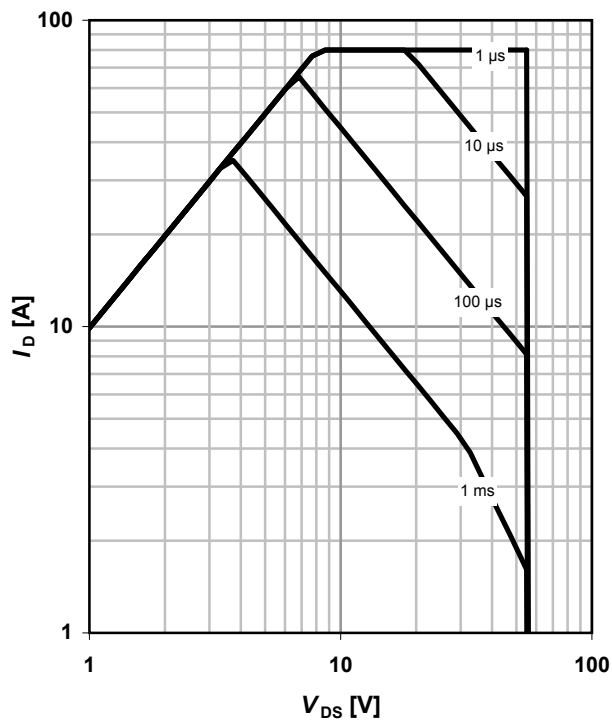
2 Drain current

$I_D = f(T_C)$; $V_{GS} \geq 6\text{ V}$; one channel active



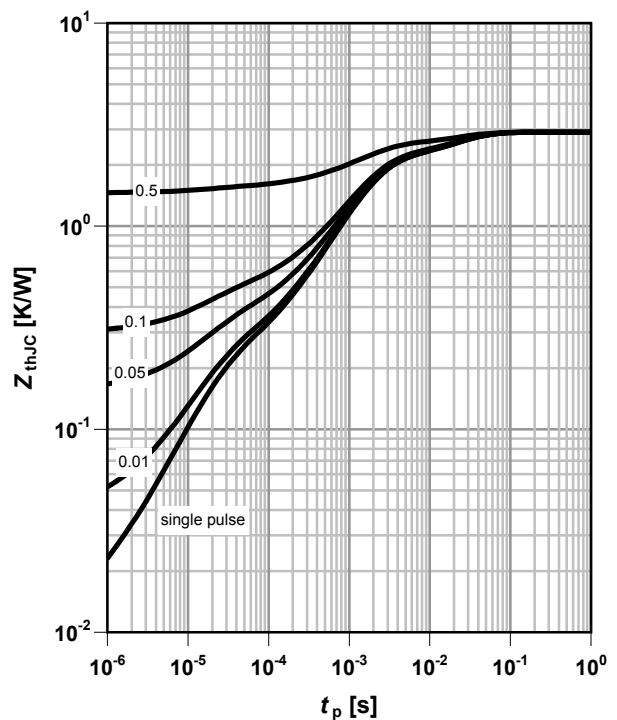
3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25^\circ\text{C}$; $D = 0$; one channel active
parameter: t_p



4 Max. transient thermal impedance

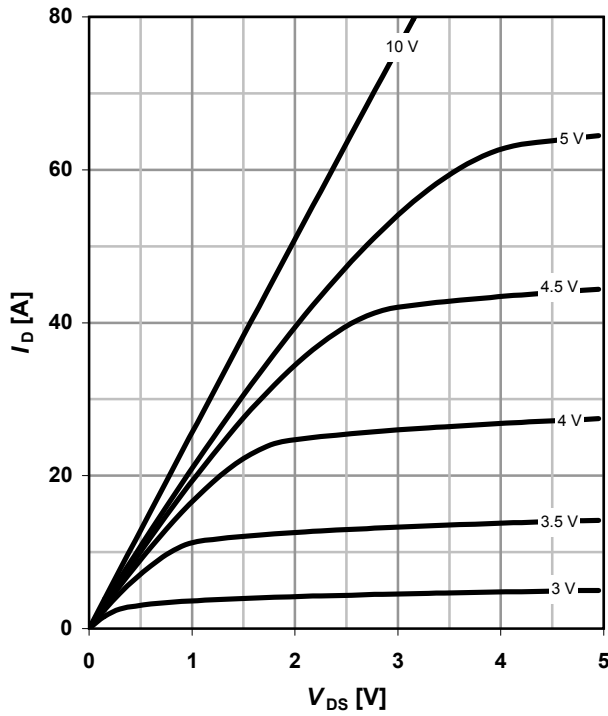
$Z_{thJC} = f(t_p)$
parameter: $D = t_p/T$



5 Typ. output characteristics⁴⁾

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

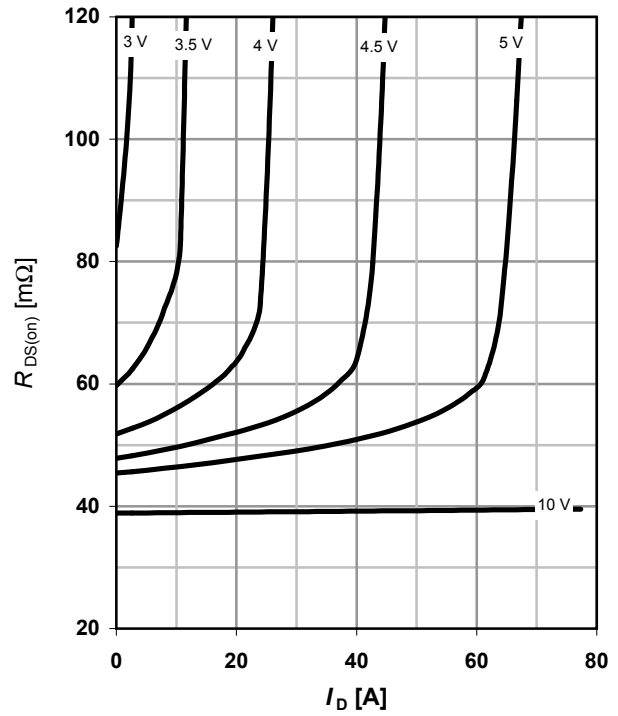
parameter: V_{GS}



6 Typ. drain-source on-state resistance⁴⁾

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

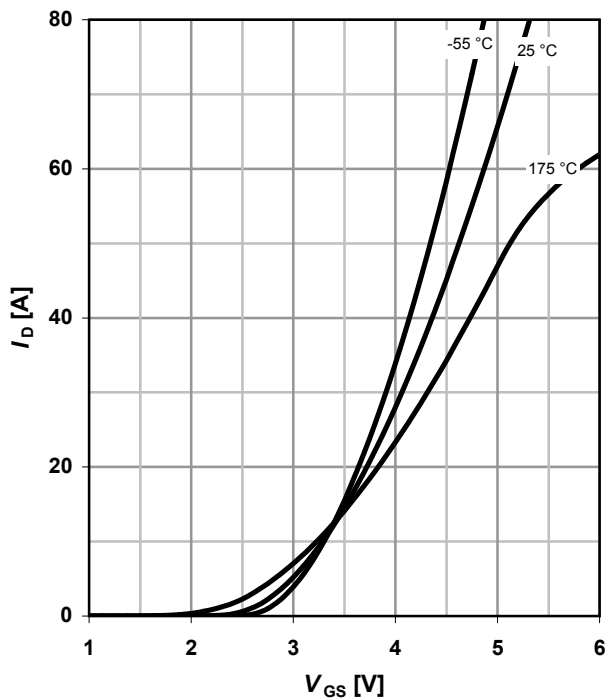
parameter: V_{GS}



7 Typ. transfer characteristics⁴⁾

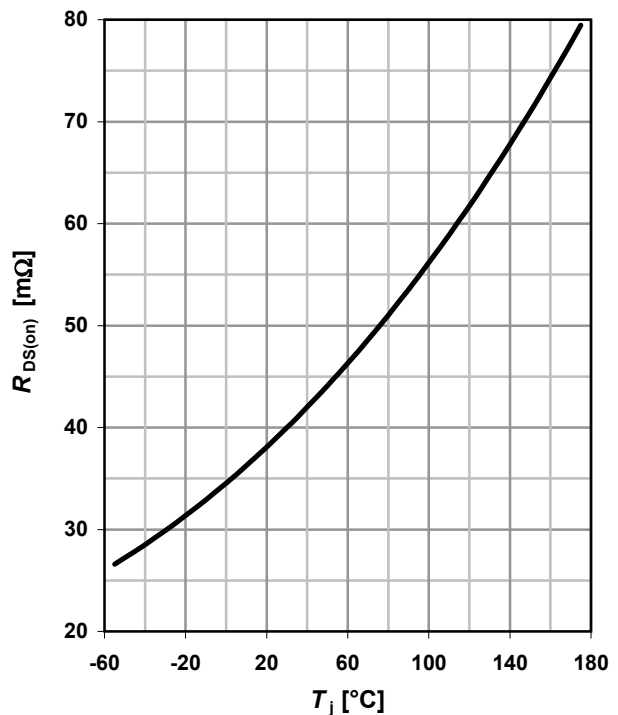
$I_D = f(V_{GS}); V_{DS} = 6V$

parameter: T_j



8 Typ. drain-source on-state resistance⁴⁾

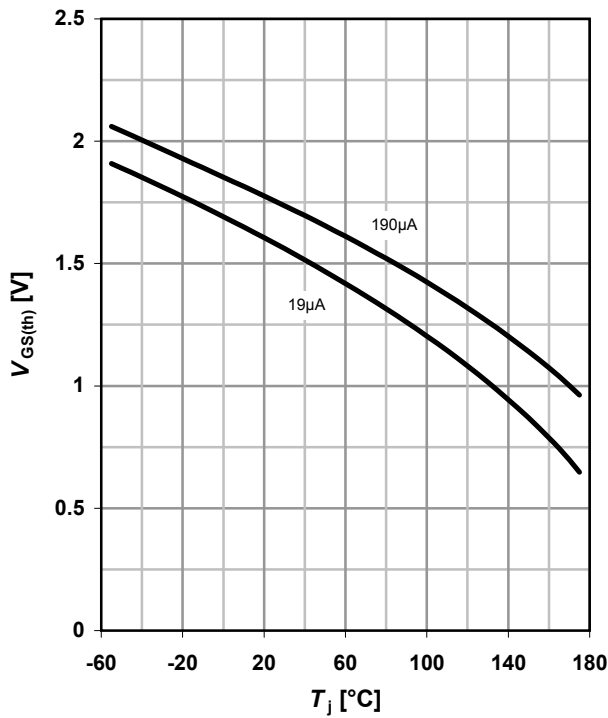
$R_{DS(on)} = f(T_j); I_D = 15\text{ A}; V_{GS} = 10\text{ V}$



9 Typ. gate threshold voltage

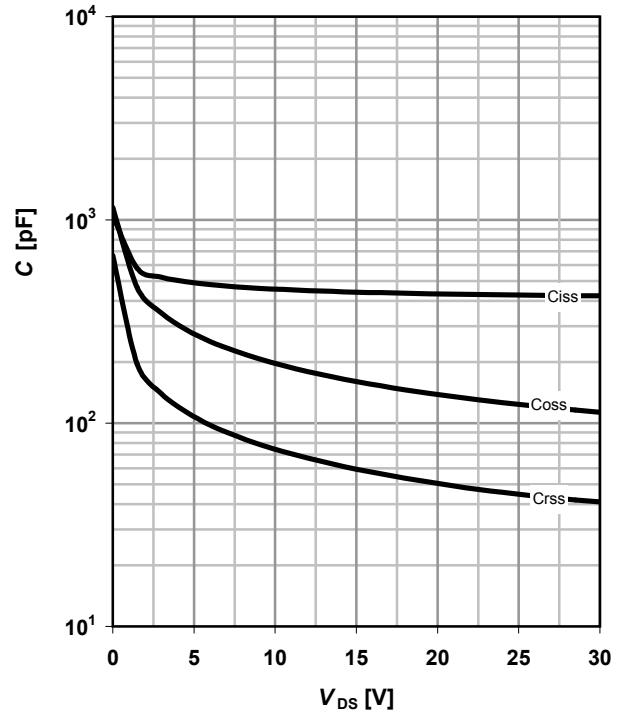
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



10 Typ. Capacitances⁴⁾

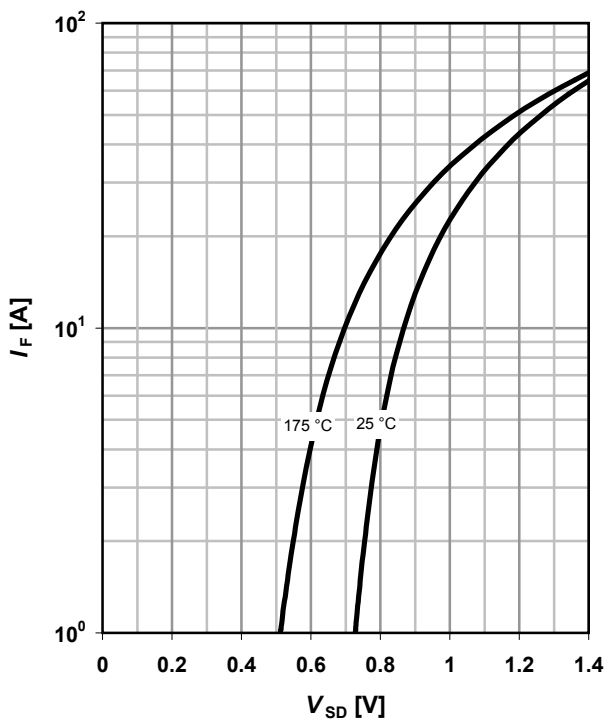
$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$



11 Typical forward diode characteristics⁴⁾

$I_F = f(V_{SD})$

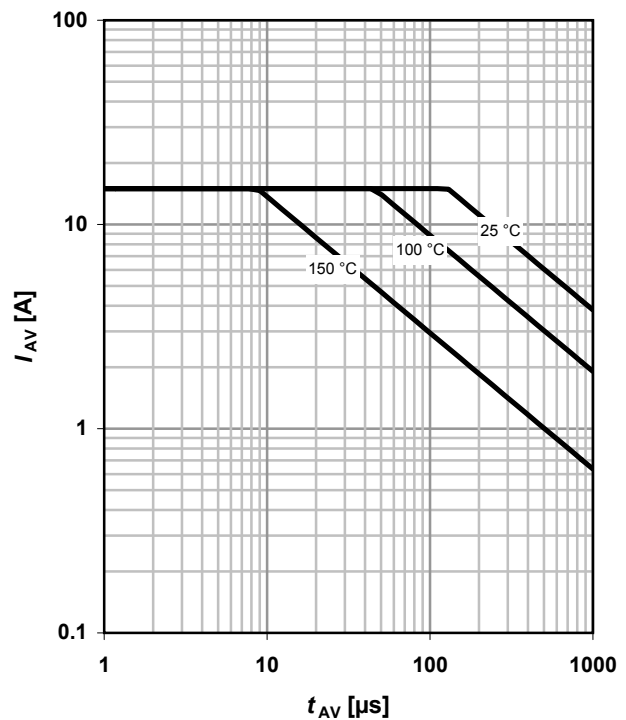
parameter: T_j



12 Avalanche characteristics⁴⁾

$I_{AS} = f(t_{AV})$

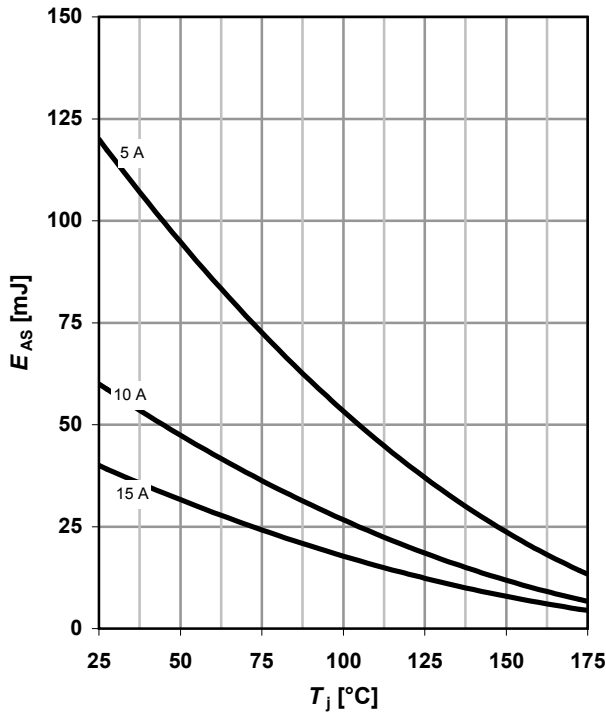
parameter: $T_{j(start)}$



13 Avalanche energy⁴⁾

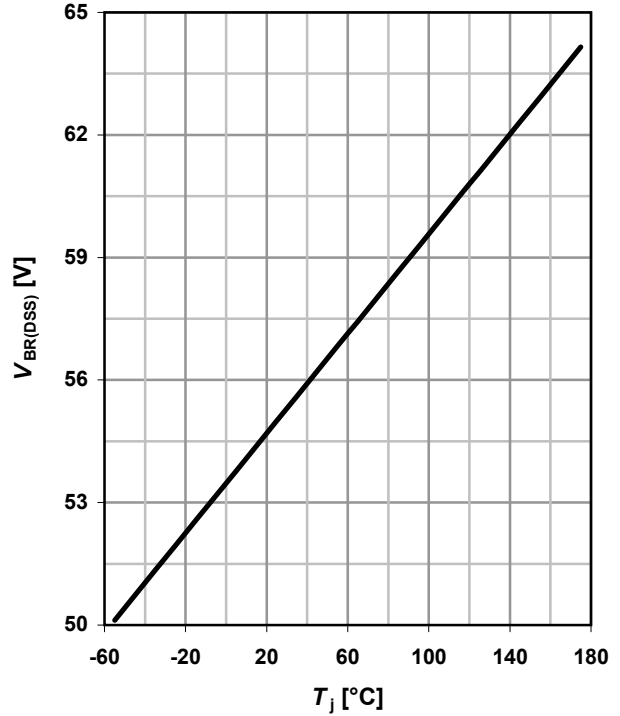
$E_{AS} = f(T_j)$

parameter: I_D



14 Drain-source breakdown voltage

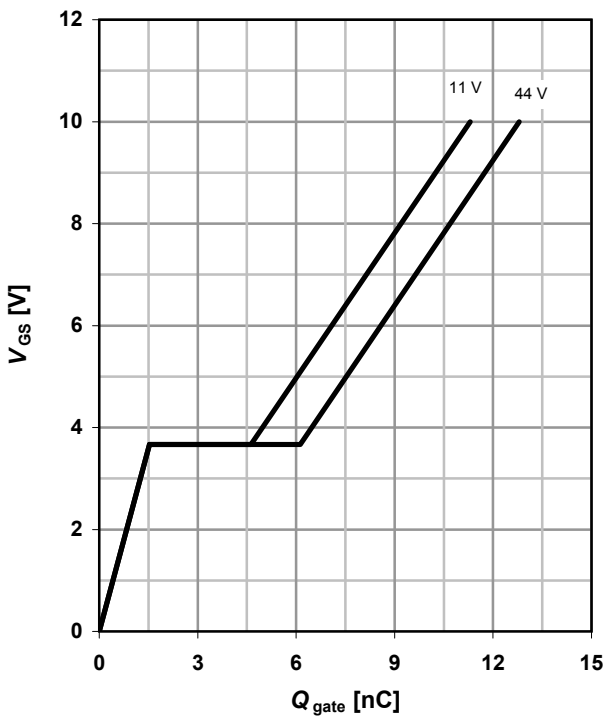
$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$



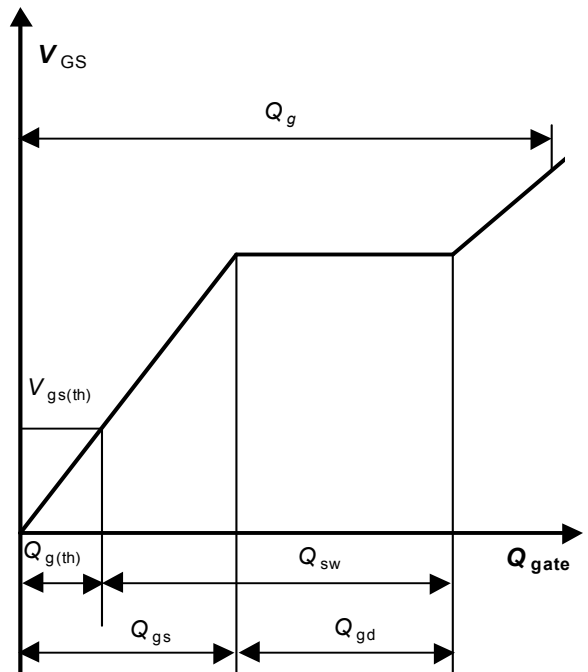
15 Typ. gate charge⁴⁾

$V_{GS} = f(Q_{gate}); I_D = 20 \text{ A pulsed}$

parameter: V_{DD}



16 Gate charge waveforms



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Revision History

| Version | Date | Changes |
|--------------|------------|------------------|
| Revision 1.0 | 07.09.2009 | Final Data Sheet |
| | | |

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